

In the Specification:

Please amend paragraph [0027] on page 8 as follows:

--A problem with the process shown in Figures 1 through 5 is that during the patterning of the bottom electrode layers 120 and 122, an etch by-product 132a or 132b may be deposited on the sidewall of the materials 120 and 122 being patterned, and on ~~one~~ the sidewalls of the dielectric hard mask 128, as shown in Figure 6. For example, if the second conductive material 122 comprises PtMn, PtMn is a noble metal that is etched by physical sputtering. A sputter-etched PtMn layer can easily be re-deposited on the sidewall, in particular when the sidewall is high and vertical.--